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# NSL05TT1

## High Current Surface Mount PNP Silicon Low $V_{CE(sat)}$ Transistor for Battery Operated Applications



ON Semiconductor™

<http://onsemi.com>

**5 VOLTS  
1.0 AMPS  
PNP TRANSISTOR**

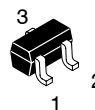
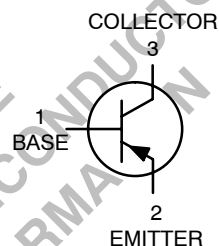
### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

| Rating                                   | Symbol    | Max                        | Unit |
|------------------------------------------|-----------|----------------------------|------|
| Collector-Emitter Voltage                | $V_{CEO}$ | -5.0                       | Vdc  |
| Collector-Base Voltage                   | $V_{CBO}$ | -10                        | Vdc  |
| Emitter-Base Voltage                     | $V_{EBO}$ | -4.0                       | Vdc  |
| Collector Current – Peak<br>– Continuous | $I_C$     | -1.0<br>-0.5               | Adc  |
| Electrostatic Discharge                  | ESD       | HBM Class 3B<br>MM Class C |      |

### THERMAL CHARACTERISTICS

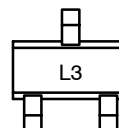
| Characteristic                                                                          | Symbol                   | Max            | Unit                       |
|-----------------------------------------------------------------------------------------|--------------------------|----------------|----------------------------|
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 1)           | 210<br>1.7     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction to Ambient                                              | $R_{\theta JA}$ (Note 1) | 595            | $^\circ\text{C/W}$         |
| Total Device Dissipation<br>$T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 2)           | 365<br>2.9     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction to Ambient                                              | $R_{\theta JA}$ (Note 2) | 340            | $^\circ\text{C/W}$         |
| Thermal Resistance,<br>Junction to Lead #3                                              | $R_{\theta JL}$          | 205            | $^\circ\text{C/W}$         |
| Junction and Storage<br>Temperature Range                                               | $T_J, T_{stg}$           | -55 to<br>+150 | $^\circ\text{C}$           |

1. FR-4 @ Minimum Pad  
2. FR-4 @ 1.0 X 1.0 inch Pad



**CASE 463  
SOT-416/SC-75  
STYLE 1**

### DEVICE MARKING



### ORDERING INFORMATION

| Device   | Package | Shipping         |
|----------|---------|------------------|
| NSL05TT1 | SOT-416 | 3000/Tape & Reel |

# NSL05TT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typical | Max | Unit |
|----------------|--------|-----|---------|-----|------|
|----------------|--------|-----|---------|-----|------|

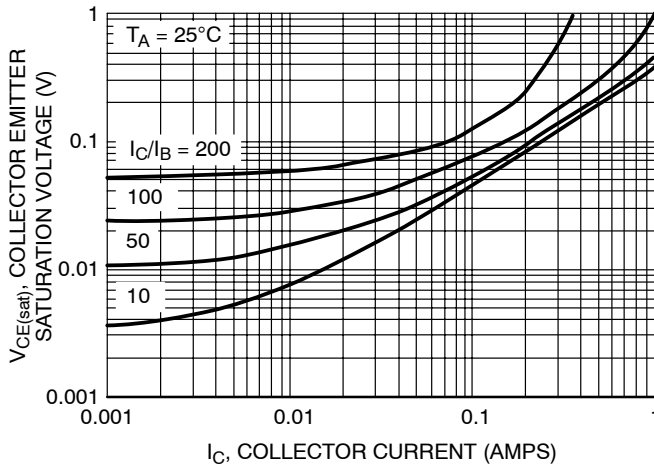
### OFF CHARACTERISTICS

|                                                                                      |                      |      |       |      |      |
|--------------------------------------------------------------------------------------|----------------------|------|-------|------|------|
| Collector–Emitter Breakdown Voltage<br>(I <sub>C</sub> = –10 mA, I <sub>B</sub> = 0) | V <sub>(BR)CEO</sub> | –5.0 | –9.0  | –    | Vdc  |
| Collector–Base Breakdown Voltage<br>(I <sub>C</sub> = –0.01 mA, I <sub>E</sub> = 0)  | V <sub>(BR)CBO</sub> | –10  | –15   | –    | Vdc  |
| Emitter–Base Breakdown Voltage<br>(I <sub>E</sub> = –0.01 mA, I <sub>C</sub> = 0)    | V <sub>(BR)EBO</sub> | –4.0 | –7.0  | –    | Vdc  |
| Collector Cutoff Current<br>(V <sub>CB</sub> = –5.0 Vdc, I <sub>E</sub> = 0)         | I <sub>CBO</sub>     | –    | –0.03 | –0.1 | μAdc |
| Collector–Emitter Cutoff Current<br>(V <sub>CES</sub> = –4.0 Vdc)                    | I <sub>CES</sub>     | –    | –0.03 | –0.1 | μAdc |
| Emitter Cutoff Current<br>(V <sub>EB</sub> = –4.0 Vdc)                               | I <sub>EBO</sub>     | –    | –0.01 | –0.1 | μAdc |

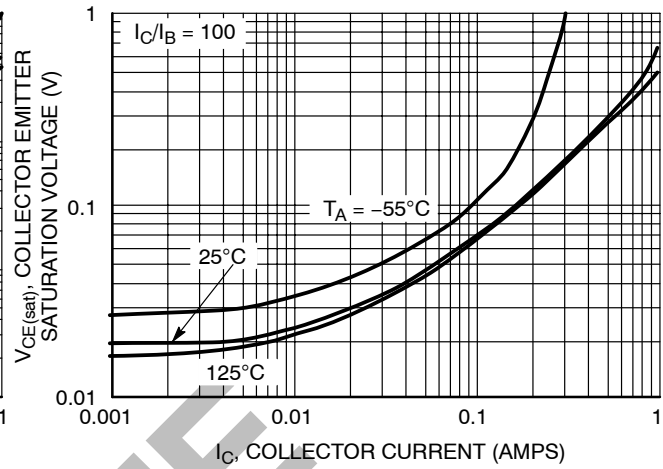
### ON CHARACTERISTICS

|                                                                                                                                                                                                                                                                                                                                                                                                                                                    |                      |                                 |                                                                    |                                                     |    |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|---------------------------------|--------------------------------------------------------------------|-----------------------------------------------------|----|
| DC Current Gain (Note 3)<br>(I <sub>C</sub> = –100 mA, V <sub>CE</sub> = –1.0 V)<br>(I <sub>C</sub> = –100 mA, V <sub>CE</sub> = –2.0 V)<br>(I <sub>C</sub> = –500 mA, V <sub>CE</sub> = –2.0 V)                                                                                                                                                                                                                                                   | h <sub>FE</sub>      | 200<br>200<br>150               | 300<br>300<br>200                                                  | –<br>–<br>–                                         |    |
| Collector–Emitter Saturation Voltage (Note 3)<br>(I <sub>C</sub> = –50 mA, I <sub>B</sub> = –0.5 mA)<br>(I <sub>C</sub> = –100 mA, I <sub>B</sub> = –1.0 mA)<br>(I <sub>C</sub> = –250 mA, I <sub>B</sub> = –2.5 mA)<br>(I <sub>C</sub> = –250 mA, I <sub>B</sub> = –5.0 mA)<br>(I <sub>C</sub> = –500 mA, I <sub>B</sub> = –5.0 mA)<br>(I <sub>C</sub> = –500 mA, I <sub>B</sub> = –50 mA)<br>(I <sub>C</sub> = –1.0 A, I <sub>B</sub> = –100 mA) | V <sub>CE(sat)</sub> | –<br>–<br>–<br>–<br>–<br>–<br>– | –0.050<br>–0.080<br>–0.130<br>–0.110<br>–0.240<br>–0.180<br>–0.340 | –0.080<br>–0.125<br>–0.200<br>–<br>–0.360<br>–<br>– | V  |
| Base–Emitter Saturation Voltage (Note 3)<br>(I <sub>C</sub> = –150 mA, I <sub>B</sub> = –20 mA)                                                                                                                                                                                                                                                                                                                                                    | V <sub>BE(sat)</sub> | –                               | –0.81                                                              | –0.9                                                | V  |
| Base–Emitter Turn–on Voltage (Note 3)<br>(I <sub>C</sub> = –150 mA, V <sub>CE</sub> = –3.0 V)                                                                                                                                                                                                                                                                                                                                                      | V <sub>BE(on)</sub>  | –                               | –0.81                                                              | –0.875                                              | V  |
| Input Capacitance<br>(V <sub>EB</sub> = 0 V, f = 1.0 MHz)                                                                                                                                                                                                                                                                                                                                                                                          | C <sub>ibo</sub>     | –                               | 55                                                                 | –                                                   | pF |
| Output Capacitance<br>(V <sub>CB</sub> = 0 V, f = 1.0 MHz)                                                                                                                                                                                                                                                                                                                                                                                         | C <sub>obo</sub>     | –                               | 38                                                                 | –                                                   | pF |
| Turn–On Time<br>(I <sub>B1</sub> = –50 mA, I <sub>C</sub> = –500 mA, R <sub>L</sub> = 3.0 Ω)                                                                                                                                                                                                                                                                                                                                                       | t <sub>on</sub>      | –                               | 60                                                                 | –                                                   | ns |
| Turn–Off Time<br>(I <sub>B1</sub> = I <sub>B2</sub> = –50 mA, I <sub>C</sub> = –500 mA, R <sub>L</sub> = 3.0 Ω)                                                                                                                                                                                                                                                                                                                                    | t <sub>off</sub>     | –                               | 100                                                                | –                                                   | ns |

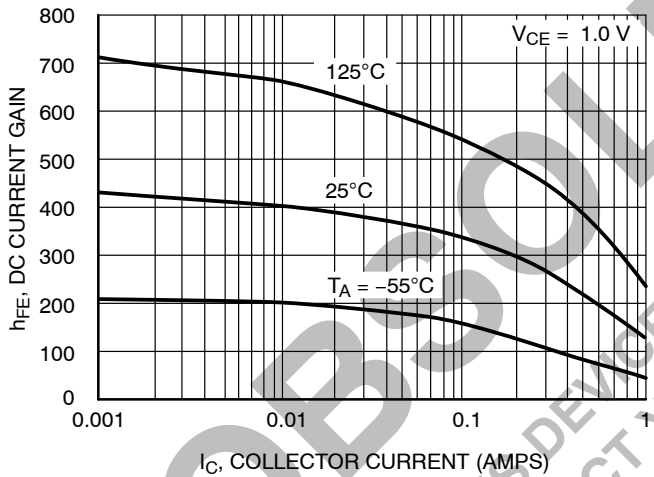
3. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%



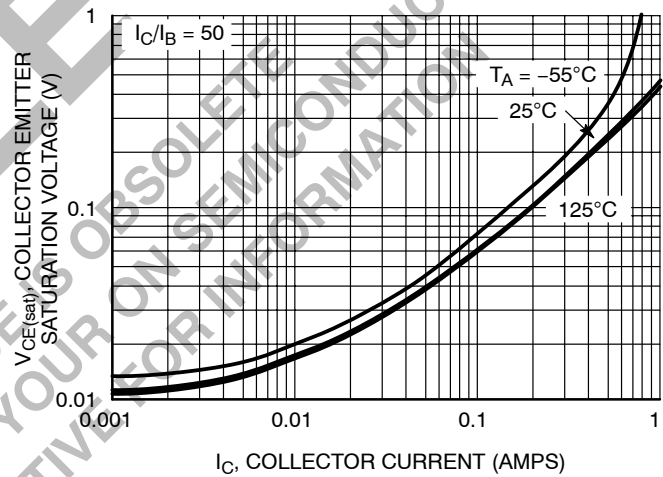
**Figure 1. Collector Emitter Saturation Voltage vs. Collector Current**



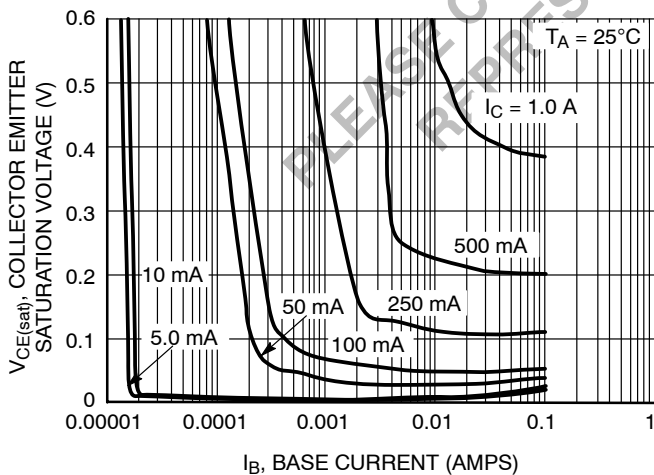
**Figure 2. Collector Emitter Saturation Voltage vs. Collector Current**



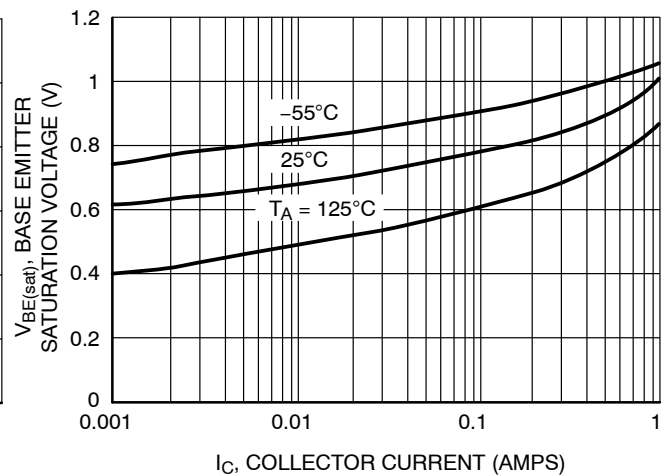
**Figure 3. DC Current Gain**



**Figure 4. Collector Emitter Saturation Voltage vs. Collector Current**

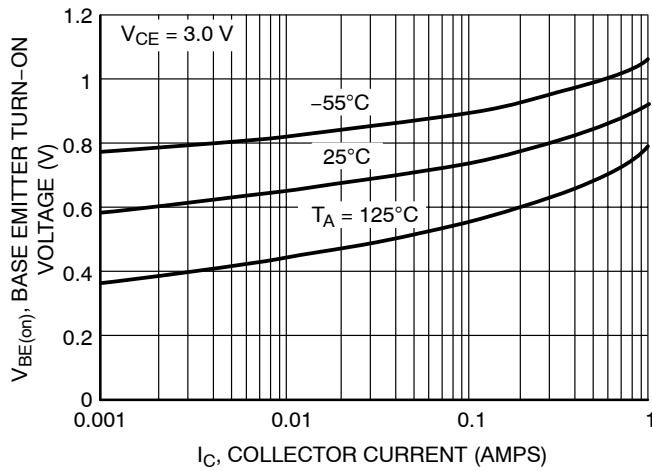


**Figure 5.  $V_{CE(sat)}$  Collector Emitter Saturation Voltage vs. Base Current**

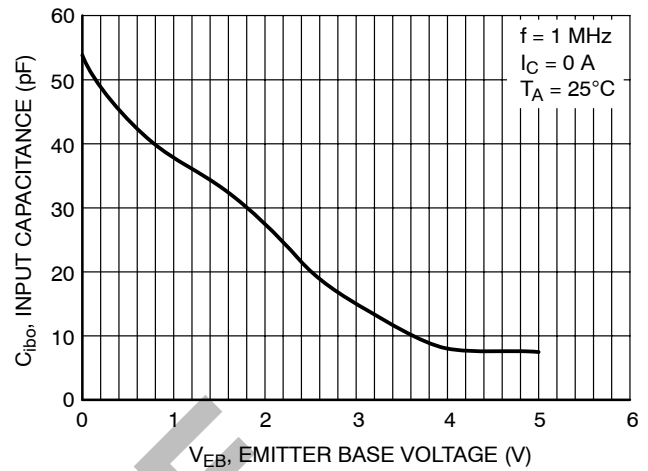


**Figure 6. Base Emitter Saturation Voltage vs. Collector Current**

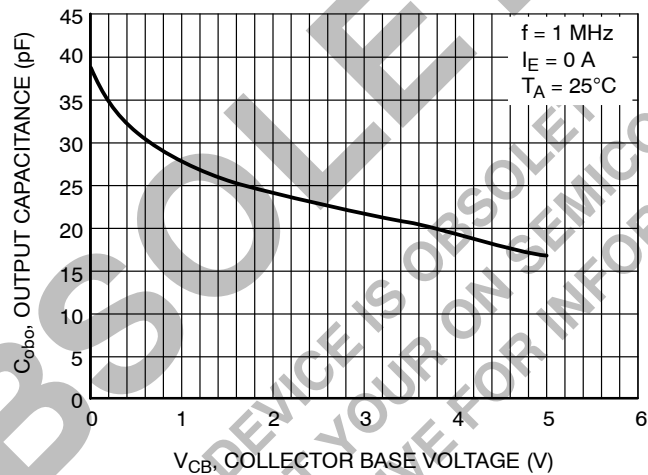
# NSL05TT1



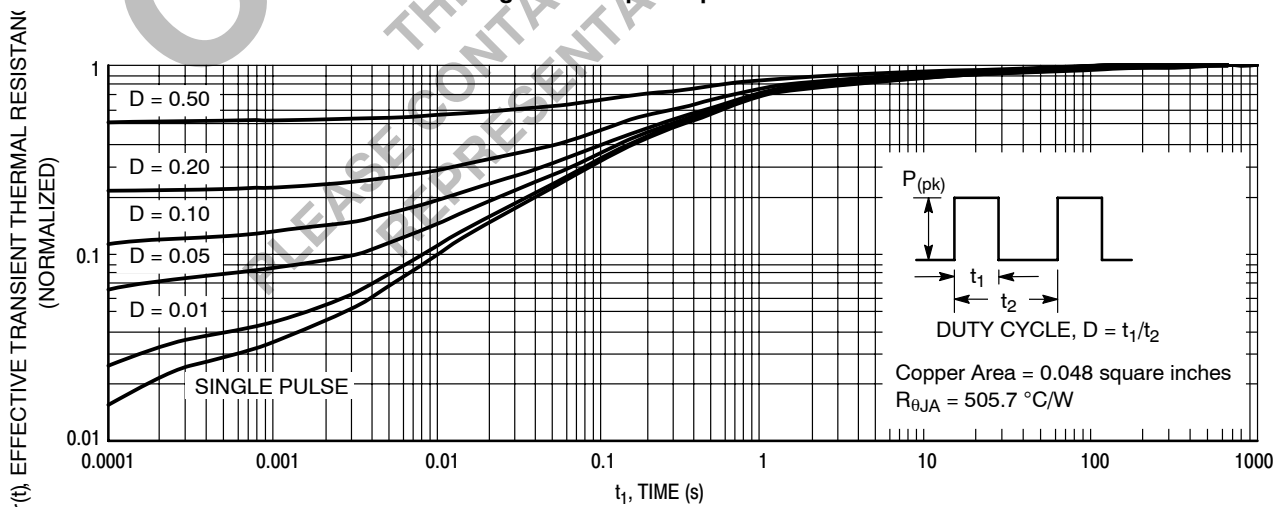
**Figure 7. Base Emitter Turn-On Voltage vs. Collector Current**



**Figure 8. Input Capacitance**



**Figure 9. Output Capacitance**

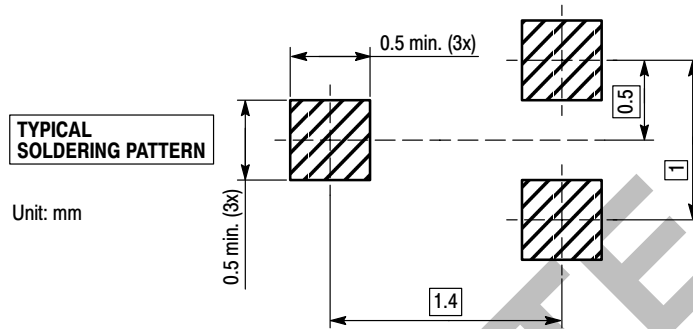


**Figure 10. Normalized Thermal Response**

## MINIMUM RECOMMENDED FOOTPRINTS FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



## SOT-416/SC-75 POWER DISSIPATION

The power dissipation of the SOT-416/SC-75 is a function of the pad size. This can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient; and the operating temperature,  $T_A$ . Using the values provided on the data sheet,  $P_D$  can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values

into the equation for an ambient temperature  $T_A$  of 25°C, one can calculate the power dissipation of the device which in this case is 210 milliwatts.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{595^\circ\text{C/W}} = 210 \text{ milliwatts}$$

The 595°C/W assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 210 milliwatts. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad®. Using a board material such as Thermal Clad, a higher power dissipation can be achieved using the same footprint.

## SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

\* \* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

## SOLDER STENCIL GUIDELINES

Prior to placing surface mount components onto a printed circuit board, solder paste must be applied to the pads. A solder stencil is required to screen the optimum amount of solder paste onto the footprint. The stencil is made of brass

or stainless steel with a typical thickness of 0.008 inches. The stencil opening size for the surface mounted package should be the same as the pad size on the printed circuit board, i.e., a 1:1 registration.

## TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating “profile” for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 11 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time.

The line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joints.

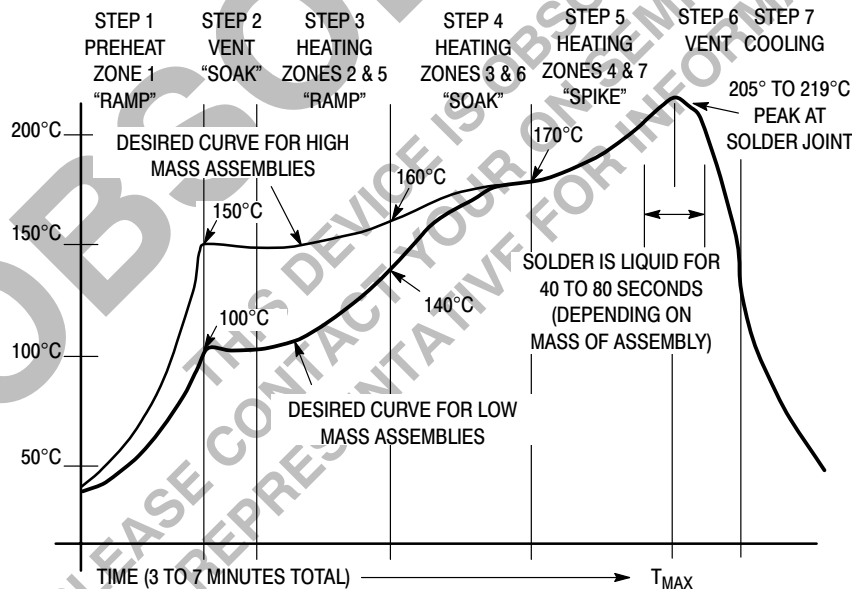
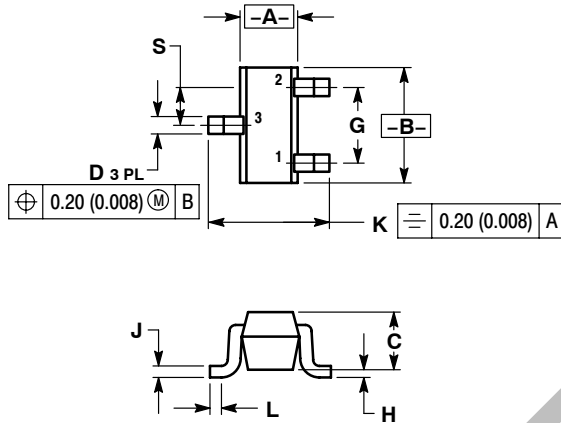


Figure 11. Typical Solder Heating Profile

# NSL05TT1

## PACKAGE DIMENSIONS

SC-75/SOT-416  
CASE 463-01  
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

| DIM | MILLIMETERS |      | INCHES    |       |
|-----|-------------|------|-----------|-------|
|     | MIN         | MAX  | MIN       | MAX   |
| A   | 0.70        | 0.80 | 0.028     | 0.031 |
| B   | 1.40        | 1.80 | 0.055     | 0.071 |
| C   | 0.60        | 0.90 | 0.024     | 0.035 |
| D   | 0.15        | 0.30 | 0.006     | 0.012 |
| G   | 1.00 BSC    |      | 0.039 BSC |       |
| H   | ---         | 0.10 | ---       | 0.004 |
| J   | 0.10        | 0.25 | 0.004     | 0.010 |
| K   | 1.45        | 1.75 | 0.057     | 0.069 |
| L   | 0.10        | 0.20 | 0.004     | 0.008 |
| S   | 0.50 BSC    |      | 0.020 BSC |       |

- STYLE 1:
- PIN 1. BASE
  - EMITTER
  - COLLECTOR

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